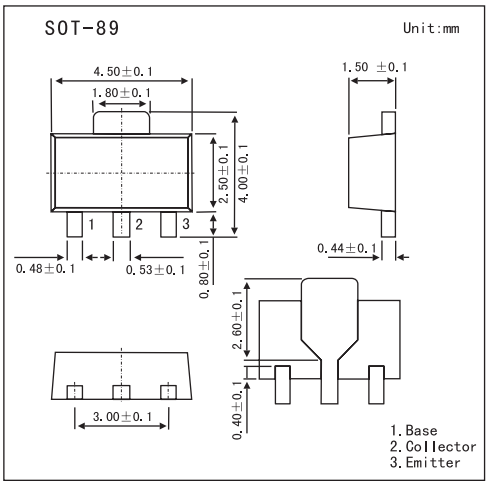
NPN Silicon Epitaxia

2SC3617



■ Features

- World standard miniature package.
- High hFE hFE=800 to 1600.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	15	V
Collector current	I_C	300	mA
Collector current (Pulse)*	I_{CP}	500	mA
Total power dissipation	P_T	2.0	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* PW≤10ms,duty cycle≤50%.

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 50V, I_E=0			100	nA
Emitter cutoff current	I_{EBO}	V_{EB} = 10V, I_C=0			100	nA
DC current gain *	h_{FE}	V_{CE} = 5.0V , I_C = 100mA	800		3200	
		V_{CE} = 5.0V , I_C = 300mA	640			
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C = 100mA , I_B = 1.0mA		0.12	0.13	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	I_C = 100mA , I_B = 1.0mA		0.7	1.2	V
Gain bandwidth product	f_T	V_{CE} = 5.0V , I_E = -50mA	150	220		MHz
Output capacitance	C_{ob}	V_{CB} = 10V , I_E = 0, f = 1.0MHz		8.0		pF

*. PW≤350μs,duty cycle≤2%

■ h_{FE} Classification

Marking	TM	TL	TK
hFE	800～1600	1200～2400	2000～3200